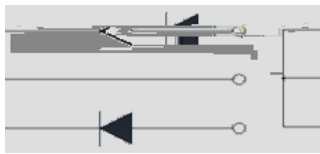
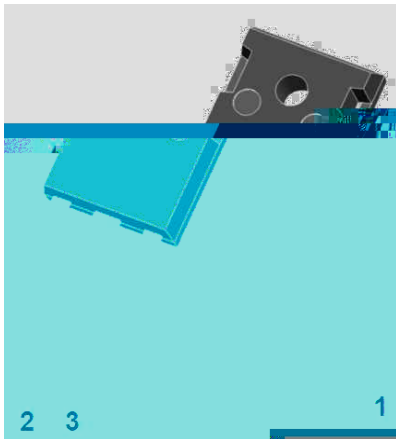


Schottky Diodes



Features

- High frequency operation
- Low forward voltage drop
- High purity , high temperature epoxy encapsulation for enhanced mechanical strength
- 7 H U P L T D P L e d leads , solderable
- 002 and J ESD22-B102
- Polarity: As marked

Maximum Ratings (T_a = 25 °C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR20200PT
Device marking code			MBR20200PT
Repetitive Peak Reverse Voltage	V _{RRM}	V	200
Average Rectified Output Current @60 H z sine wave , R-load = 15 °	I _O	A	20
Surge(Non-repetitive)Forward Current @60 H z half sine-wave , 1 cycle , T _a = 25 °	I _{FSM}	A	200
Current S q u a r e d Time @1ms ≤ t ≤ 8.3ms T _j ≤ 25 °	I ² t	A ² s	166
Storage Temperature	T _{stg}	°C	- 5 5 ~ + 17 5
J unction Temperature	T _j	°C	- 5 5 ~ + 17 5

Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Min	Typ	Max
Peak Forw = 10.0A T _j = 125 °C			0.68	0.72		
DC reverse current at rated DC blocking voltage per diode	I _{RRM1}			-	-	20
J unction capacitance	C _j		1MH Z Applied Voltage V.D.C. and Reverse of 4.0	100	158	300

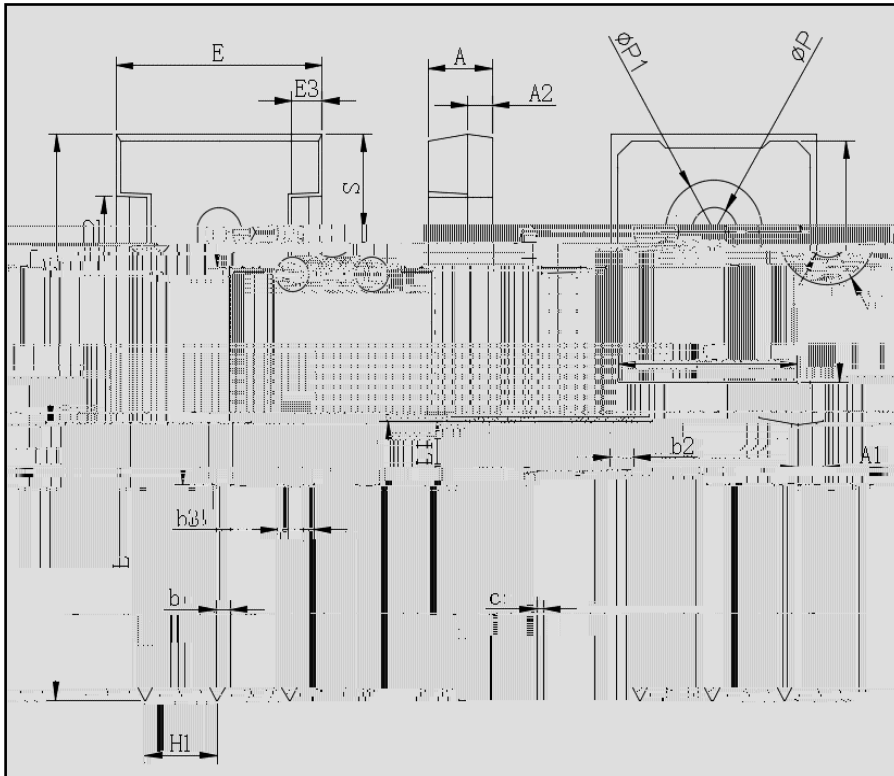
Note1:Pulse test:300uS pulse width , 1% duty cycle

Note2:Pulse test:pulse width 40mS



MBR20200PT

Outline Dimensions



TO-247AB		
Dim	Min	Max
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.0	1.4
b2	1.91	2.21
C	0.5	0.7
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.0	13.6
E2	4.80	5.20
E3	2.30	2.70
L	19.62	20.22
L1	-	4.30
$\bar{u}P$	3.40	3.80
$\bar{u}P1$	-	7.30
S	6.15 TYP	
H1	5.44TYP	
b3	2.80	3.20

